

Ordering number : ENN6913

PNP / NPN Epitaxial Planar Silicon Transistors

2SA2040 / 2SC5707

High Current Switching Applications

Applications

- DC-DC converter, relay drivers, lamp drivers, motor drivers, strobes.

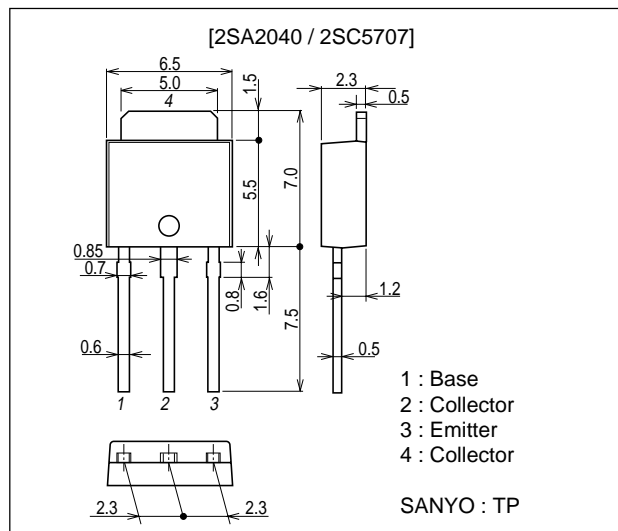
Features

- Adoption of FBET, MBIT process.
- Large current capacitance.
- Low collector-to-emitter saturation voltage.
- High-speed switching.
- High allowable power dissipation.

Package Dimensions

unit : mm

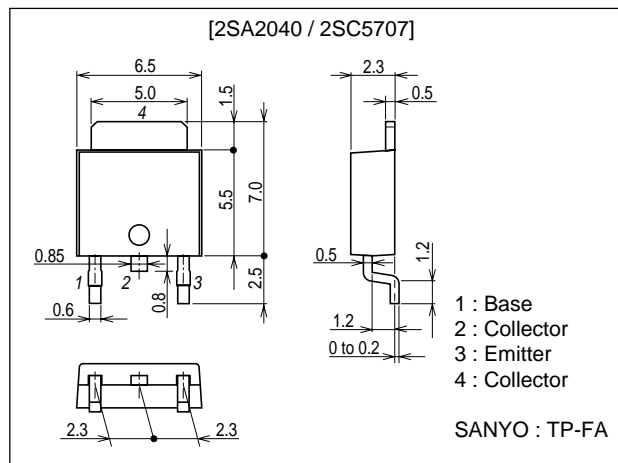
2045B



Package Dimensions

unit : mm

2044B



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30101 TS IM TA-3233 No.6913-1/5

Specifications

Note*() : 2SA2040

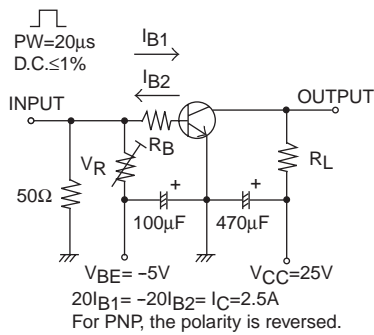
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CB0}		(-50)80	V
Collector-to-Emitter Voltage	V _{CES}		(-50)80	V
Collector-to-Emitter Voltage	V _{CEO}		(-)50	V
Emitter-to-Base Voltage	V _{EBO}		(-)6	V
Collector Current	I _C		(-)8	A
Collector Current (Pulse)	I _{CP}		(-)11	A
Base Current	I _B		(-)2	A
Collector Dissipation	P _C		1.0	W
		T _c =25°C	15	W
Junction Temperature	T _J		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

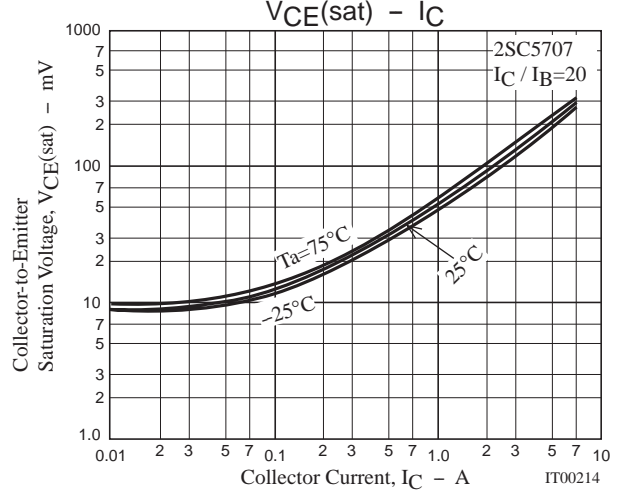
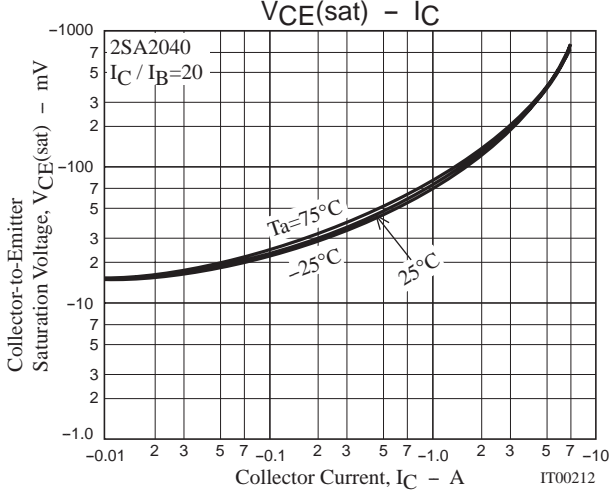
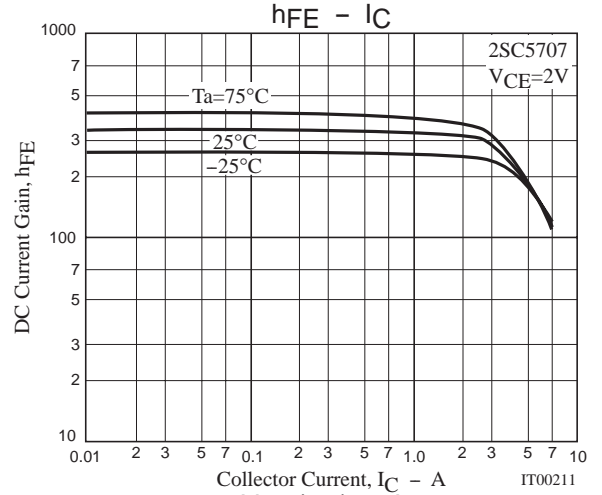
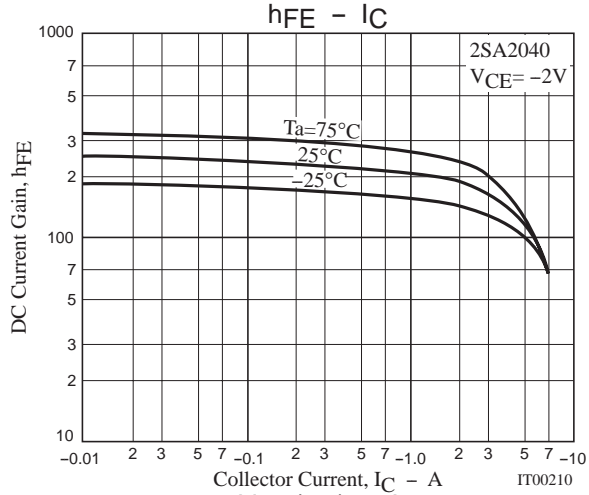
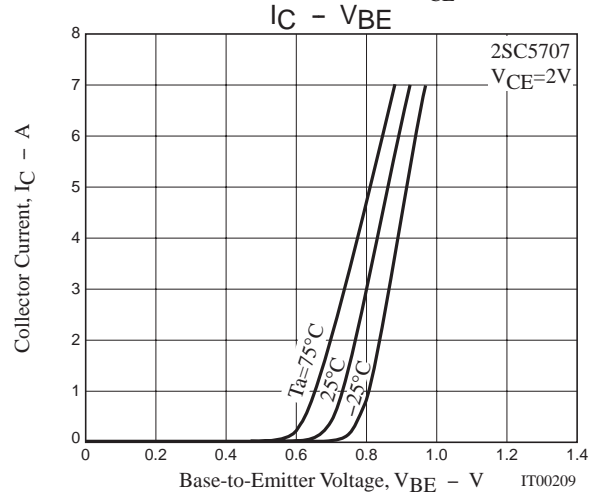
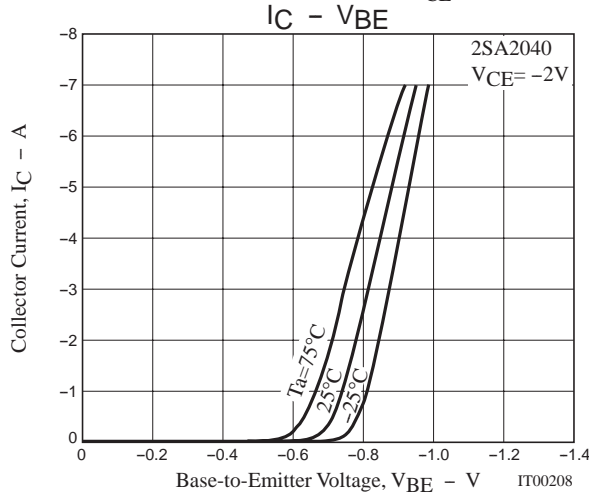
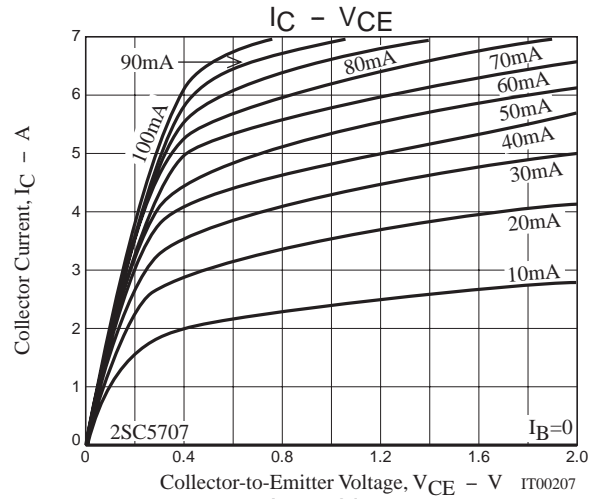
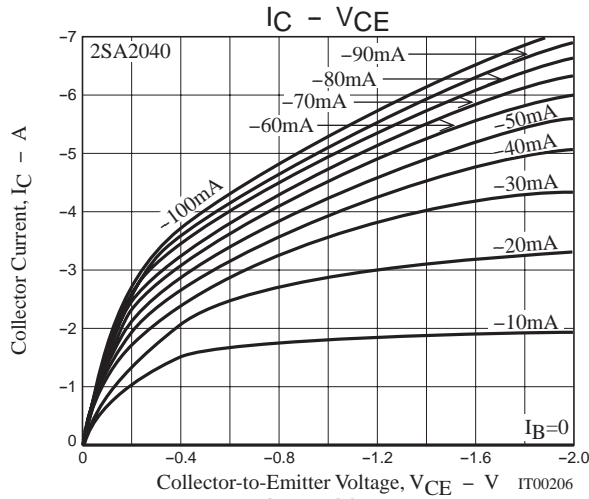
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I _{CBO}	V _{CB} =(-)40V, I _E =0			(-)0.1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =(-)4V, I _C =0			(-)0.1	μA
DC Current Gain	h _{FE}	V _{CE} =(-)2V, I _C =(-)500mA	200		560	
Gain-Bandwidth Product	f _T	V _{CE} =(-)10V, I _C =(-)500mA		(290)330		MHz
Output Capacitance	C _{ob}	V _{CB} =(-)10V, f=1MHz		(50)28		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =(-)3.5A, I _B =(-)175mA		(-230)160	(-390)240	mV
		I _C =(-)2A, I _B =(-)40mA		(-240)110	(-400)170	mV
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =(-)2A, I _B =(-)40mA		(-)0.83	(-)1.2	V
Collector-to-Base Breakdown Voltage	V _{(BR)CBO}	I _C =(-)10μA, I _E =0	(-50)80			V
Collector-to-Emitter Breakdown Voltage	V _{(BR)CES}	I _C =(-)100μA, R _{BE} =∞	80			V
Collector-to-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =(-)1mA, R _{BE} =∞	(-)50			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =(-)10μA, I _C =0	(-)6			V
Turn-On Time	t _{on}	See specified test circuit.		(40)30		ns
Storage Time	t _{stg}	See specified test circuit.		(225)420		ns
Fall Time	t _f	See specified test circuit.		25		ns

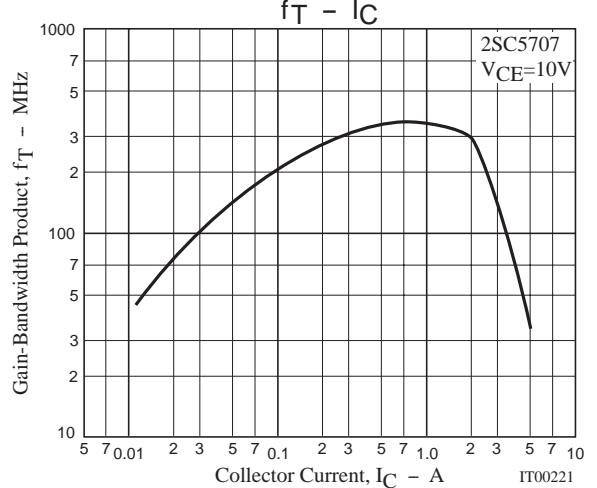
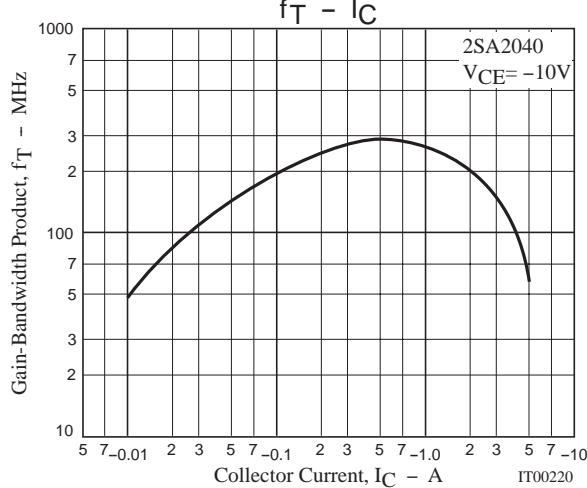
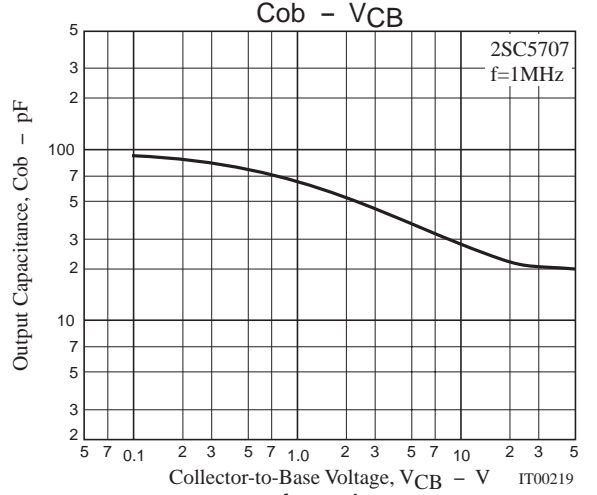
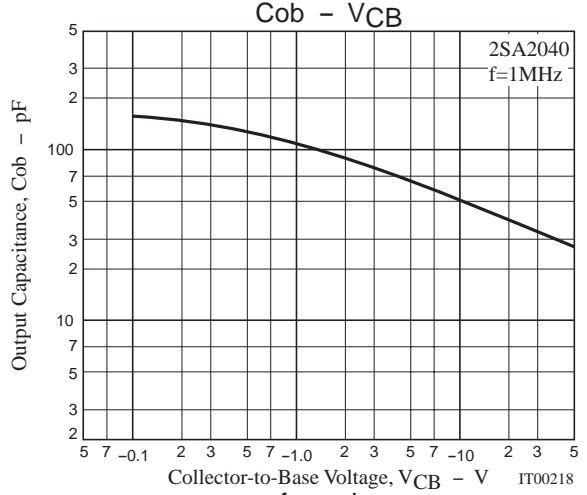
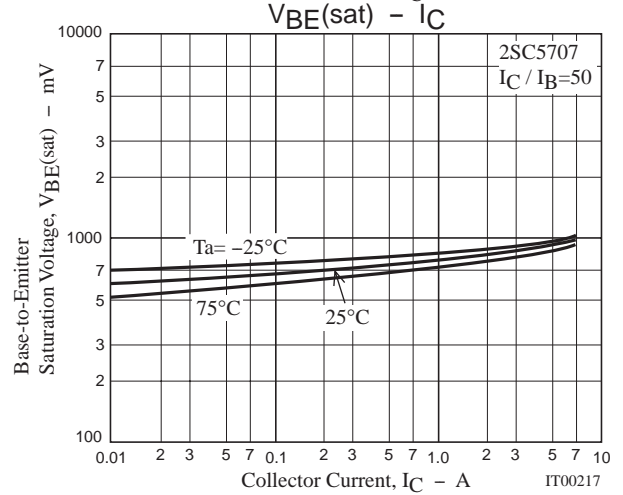
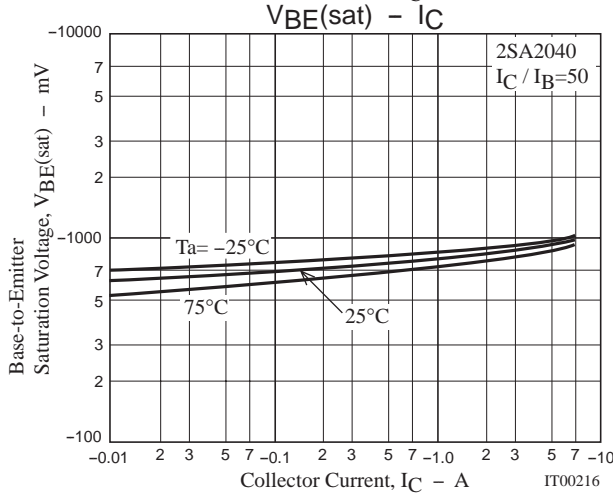
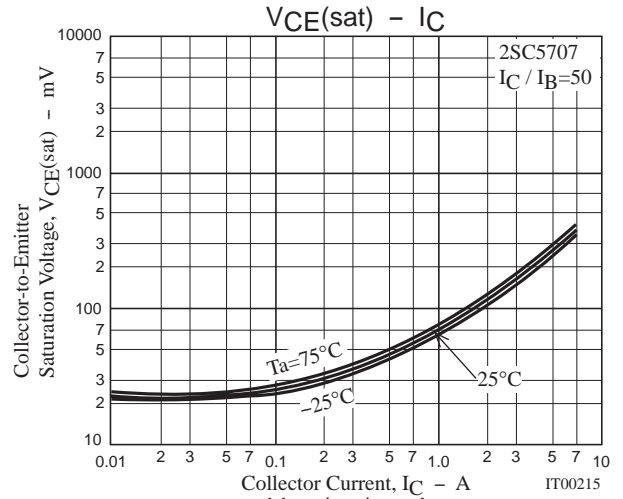
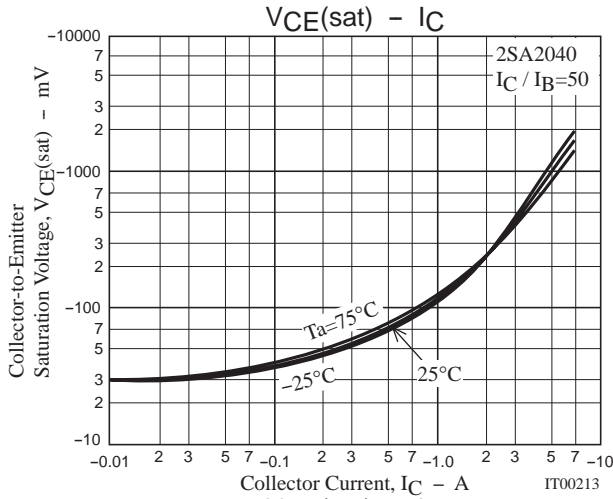
Swiching Time Test Circuit



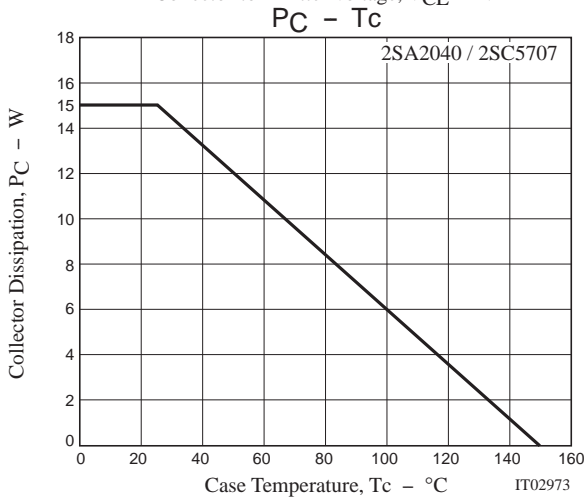
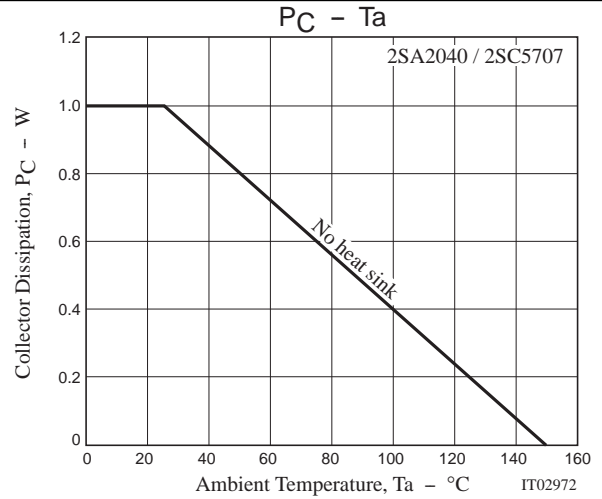
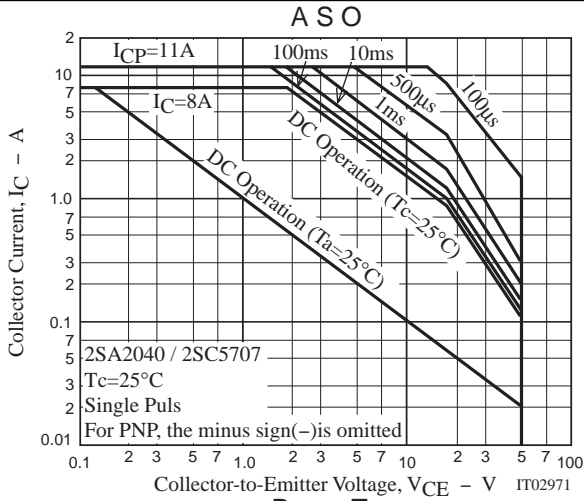
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